WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a first semiconductor layer formed in a first region of a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said first semiconductor layer; and

a plurality of second semiconductor layers formed in second regions of said semiconductor substrate.

2. A semiconductor device according to claim 1, wherein at least a portion of said plurality of second semiconductor layers is formed within the range of a radius of 5 mm from a certain point on said first semiconductor layer.

3. A semiconductor device according to claim 1, wherein each of said plurality of second semiconductor layers is surrounded by said first semiconductor layer.

4. A semiconductor device according to claim 1, wherein a logic circuit is formed in said first semiconductor layer, and at least one of a storage element, analog element, and signal input/output circuit is formed in said plurality of second semiconductor layers.

5. A semiconductor device according to claim 1, wherein one of said plurality of second semiconductor layers surrounds said first semiconductor layer.

6. A semiconductor device according to claim 1,

wherein said plurality of second semiconductor layers are arranged to be symmetrical with respect to a certain point on said semiconductor substrate.

7. A semiconductor device according to claim 1, wherein said plurality of second semiconductor layers are arranged to be symmetrical with respect to a certain straight line on said semiconductor substrate.

8. A semiconductor device in which a plurality of semiconductor devices according to claim 1 are laid out.

9. A semiconductor device according to claim 1, wherein one of said plurality of second semiconductor layers is formed on an outerperipheral of said semiconductor substrate.

10. A semiconductor device in which a plurality of semiconductor devices according to claim 9 are laid out.

11. A semiconductor device according to claim 1, wherein the sum of the areas of said plurality of second semiconductor layers is larger than the area of said first semiconductor layer.

12. A semiconductor device according to claim 1, wherein said plurality of second semiconductor layers are deposited by epitaxial growth.

13. A semiconductor device comprising:

a plurality of first semiconductor layers formed in a first region of a semiconductor substrate with one

of an insulating film and a cavity interposed between said semiconductor substrate and said plurality of first semiconductor layers; and

a second semiconductor layer formed in a second region of said semiconductor substrate.

14. A semiconductor device according to claim 13, wherein at least a portion of said second semiconductor layer is formed within the range of a radius of 5 mm from a certain point on said plurality of first semiconductor layers.

15. A semiconductor device according to claim 13, wherein each of said plurality of first semiconductor layers is surrounded by said second semiconductor layer.

16. A semiconductor device according to claim 13, wherein logic circuits are formed in said plurality of first semiconductor layers, and at least one of a storage element, analog element, and signal input/output circuit is formed in said second semiconductor layer.

17. A semiconductor device according to claim 13, wherein said plurality of first semiconductor layers are arranged to be symmetrical with respect to a certain point on said semiconductor substrate.

18. A semiconductor device according to claim 13, wherein said plurality of first semiconductor layers are arranged to be symmetrical with respect to a

certain straight line on said semiconductor substrate.

19. A semiconductor device according to claim 13, wherein the area of said second semiconductor layer is larger than the sum of the areas of said plurality of first semiconductor layers.

20. A semiconductor device according to claim 13, wherein said second semiconductor layer is deposited by epitaxial growth.

21. A semiconductor device comprising:

a first semiconductor layer formed on a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said first semiconductor layer, said first semiconductor layer being a rectangle; and

a second semiconductor layer formed on an outerperipheral of said semiconductor substrate, said second semiconductor layer surrounding said first semiconductor layer, said second semiconductor layer extending to a corner of said first semiconductor layer.

22. A semiconductor device according to claim 21, wherein the area of said second semiconductor layer is larger than the area of said first semiconductor layer.

23. A semiconductor device according to claim 21, wherein said second semiconductor layer is deposited by epitaxial growth.

24. A semiconductor device comprising:

a first semiconductor layer formed in a first region of a semiconductor substrate with an insulating film interposed between said semiconductor substrate and said first semiconductor layer; and

a second semiconductor layer formed in a second region of said semiconductor substrate, at least a portion of said second semiconductor layer being formed within the range of a radius of 5 mm from any point on said first semiconductor layer.